

Amendments to the Specification:

Please replace the paragraph at 1, line 5 to line 15 with the following new paragraph:

This application claims the benefit of U.S. Provisional Patent Application No. 60/469,433 filed May 9, 2003 naming Tipton et al. and titled “Method of Porogen Removal from Porous Low-K Films Using UV Irradiation,” and this This application is a continuation-in-part claiming priority under 35 USC 120 from US Patent Application No. 10/404,693, filed on March 31, 2003, titled “Method for Forming Porous Films by Porogen Removal Combined with In Situ Surface Modification,” by Raashina Humayun et al. as inventors, which application is Both applications are incorporated herein by reference in their entireties its entirety for all purposes. This application is also related to US Patent Application No. 10/672,305 _____ (~~Attorney Docket NOVLP069~~) filed on the same day as the instant application, titled “Method for Removal of Porogens from Porous Low-k Films Using Supercritical Fluids,” by Adrienne Tipton et al. as inventors and to US Patent Application No. 10/295,965 filed November 15, 2002 by Schulberg, et al., and titled “System for Deposition of Mesoporous Materials,” which applications are incorporated herein by reference in its entirety for all purposes.